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(54) **FORMING A CONDUCTIVE STRUCTURE IN A SEMICONDUCTOR DEVICE**

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(*) Notice: This patent issued on a continued prosecution application filed under 37 CFR 1.53(d), and is subject to the twenty year patent term provisions of 35 U.S.C. 154(a)(2).

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Related U.S. Application Data

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(51) **Int. Cl.**⁷ **H01L 21/4763**

(52) **U.S. Cl.** **438/591; 438/585**

(58) **Field of Search** 438/591, 585

(57) **ABSTRACT**

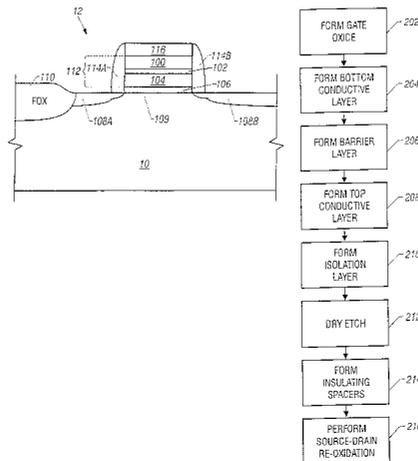
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A conductive structure for use in a semiconductor device includes a multilayer structure. A first layer includes a material containing silicon, e.g., polysilicon and silicon germanide. A barrier layer is formed over the first layer, with the barrier layer including metal silicide or metal silicide nitride. A top conductive layer is formed over the barrier layer. The top conductive layer can include metal or metal silicide. Selective oxidation can be performed to reduce the amount of oxidation of selected materials in a structure containing multiple layers, such as the multilayer conductive structure. The selective oxidation is performed in a single-wafer rapid thermal processing system, in which a selected ambient, including hydrogen, is used to ensure low oxidation of a selected material, such as tungsten or a metal nitride.

25 Claims, 6 Drawing Sheets



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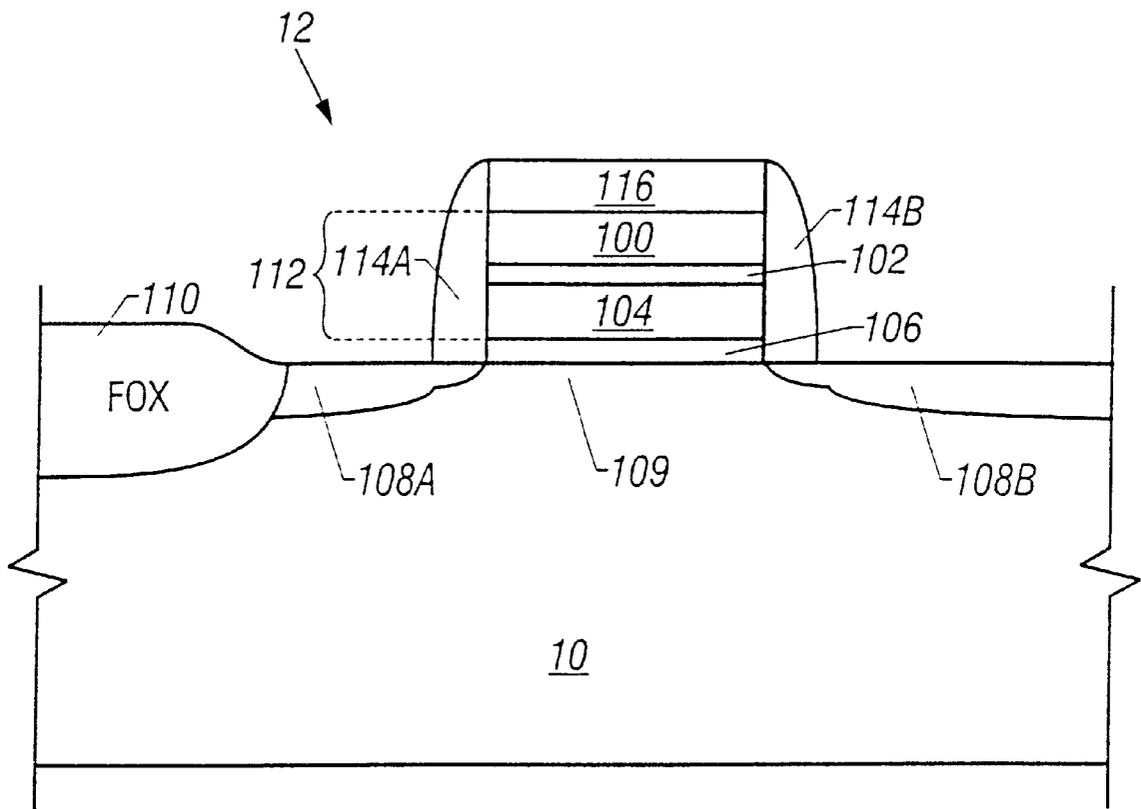


FIGURE 1

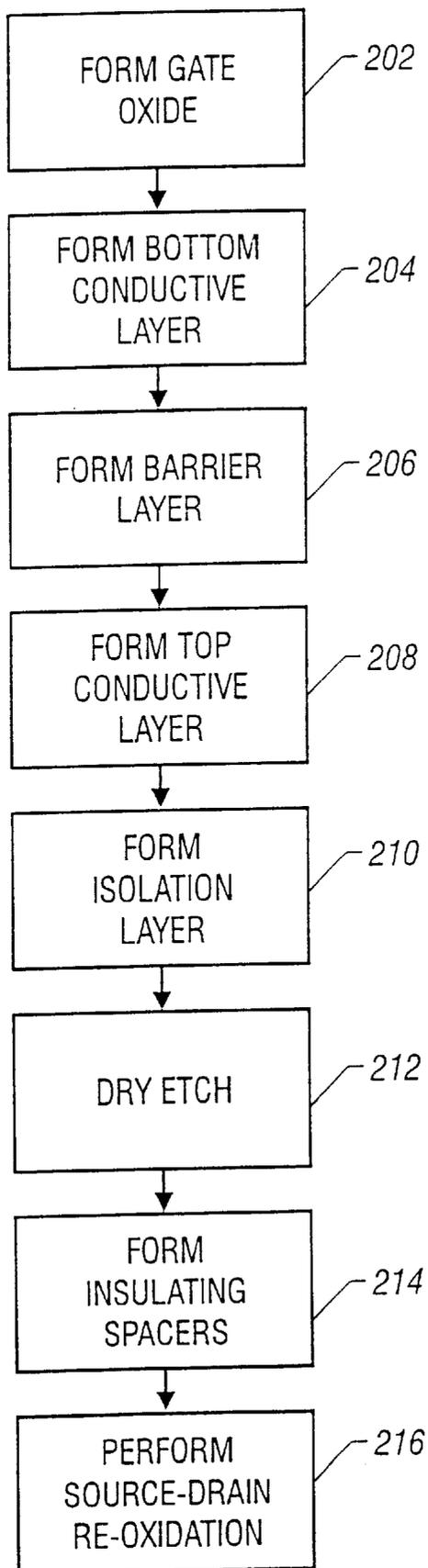


FIGURE 2

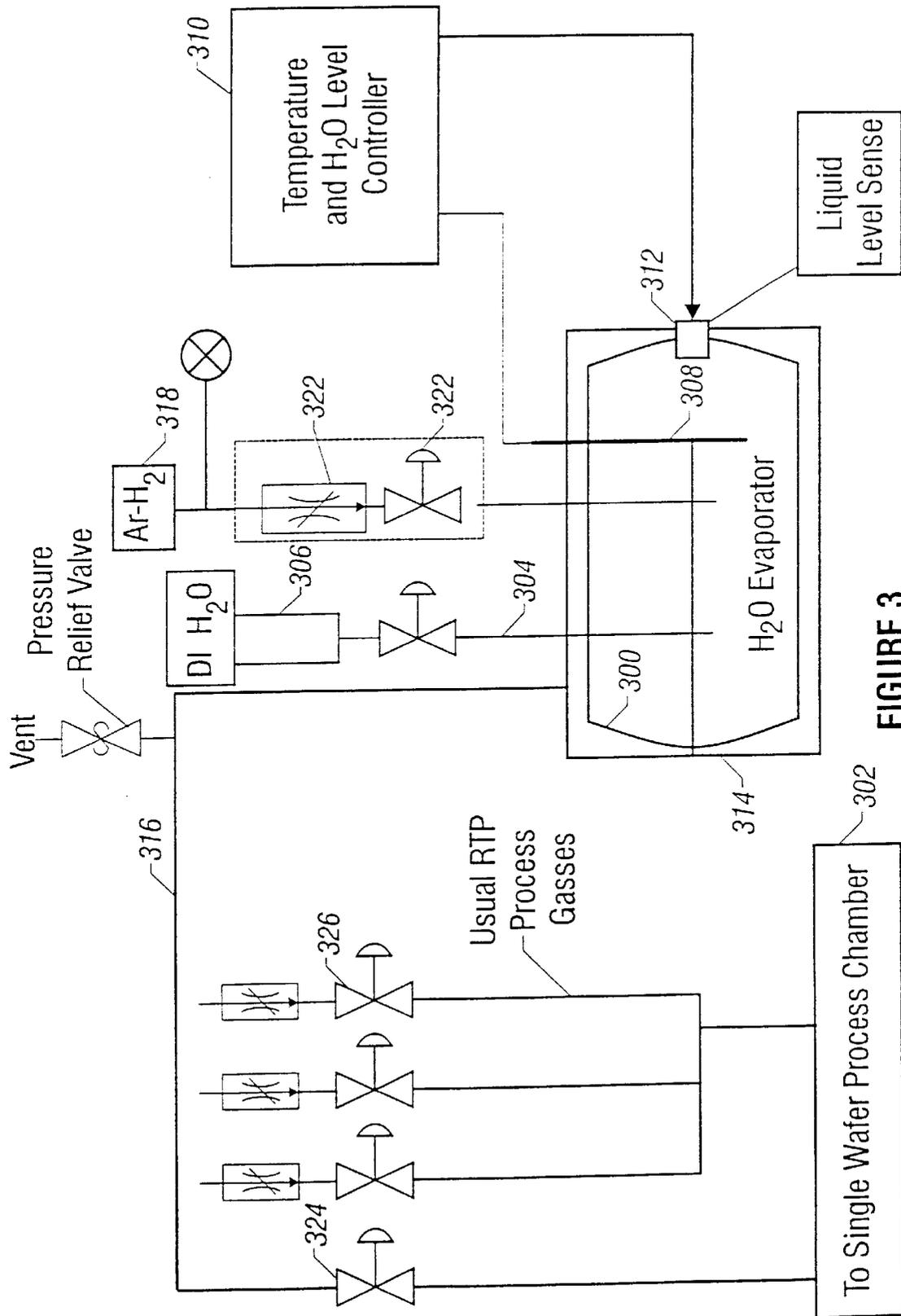


FIGURE 3

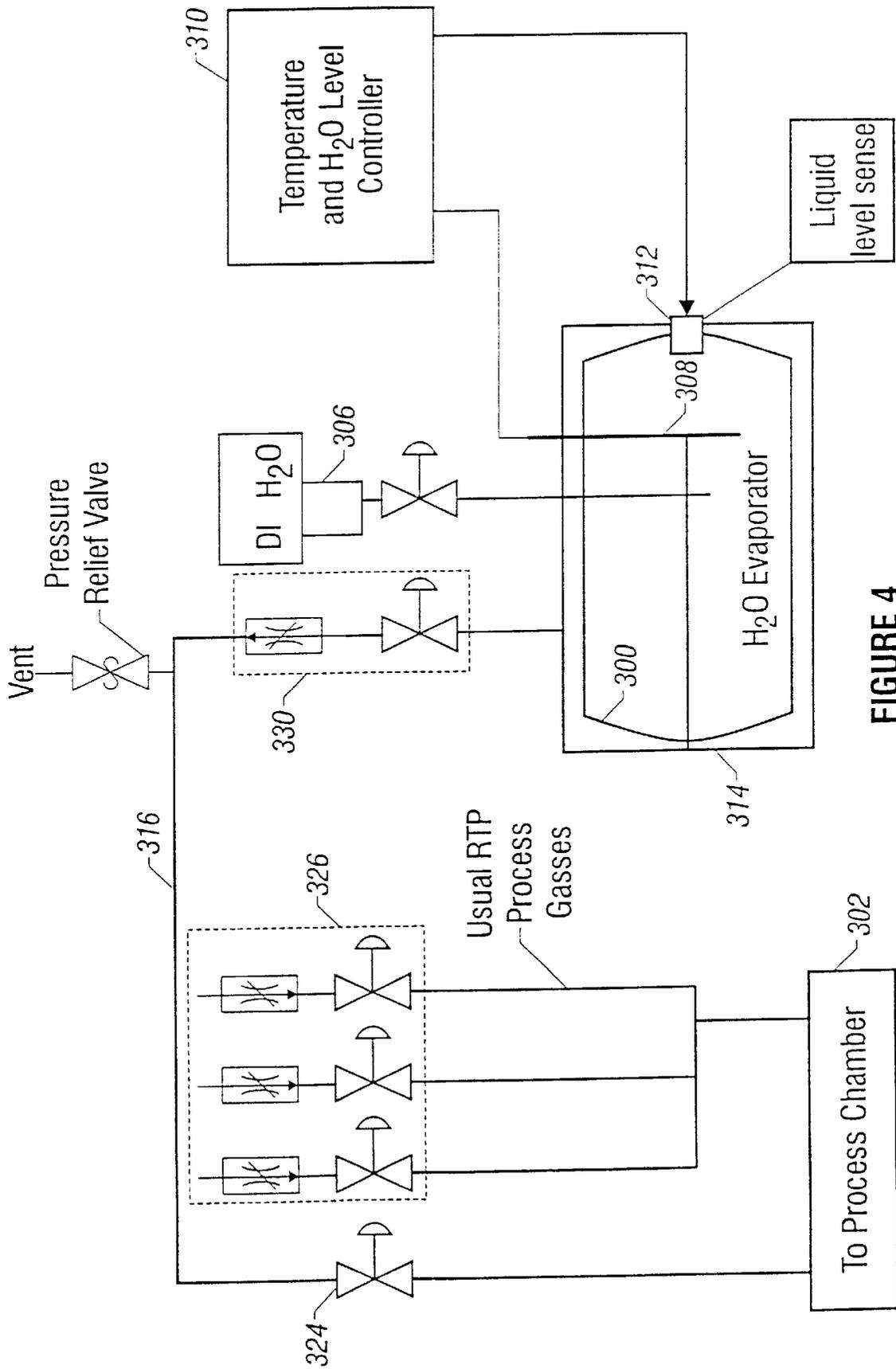


FIGURE 4

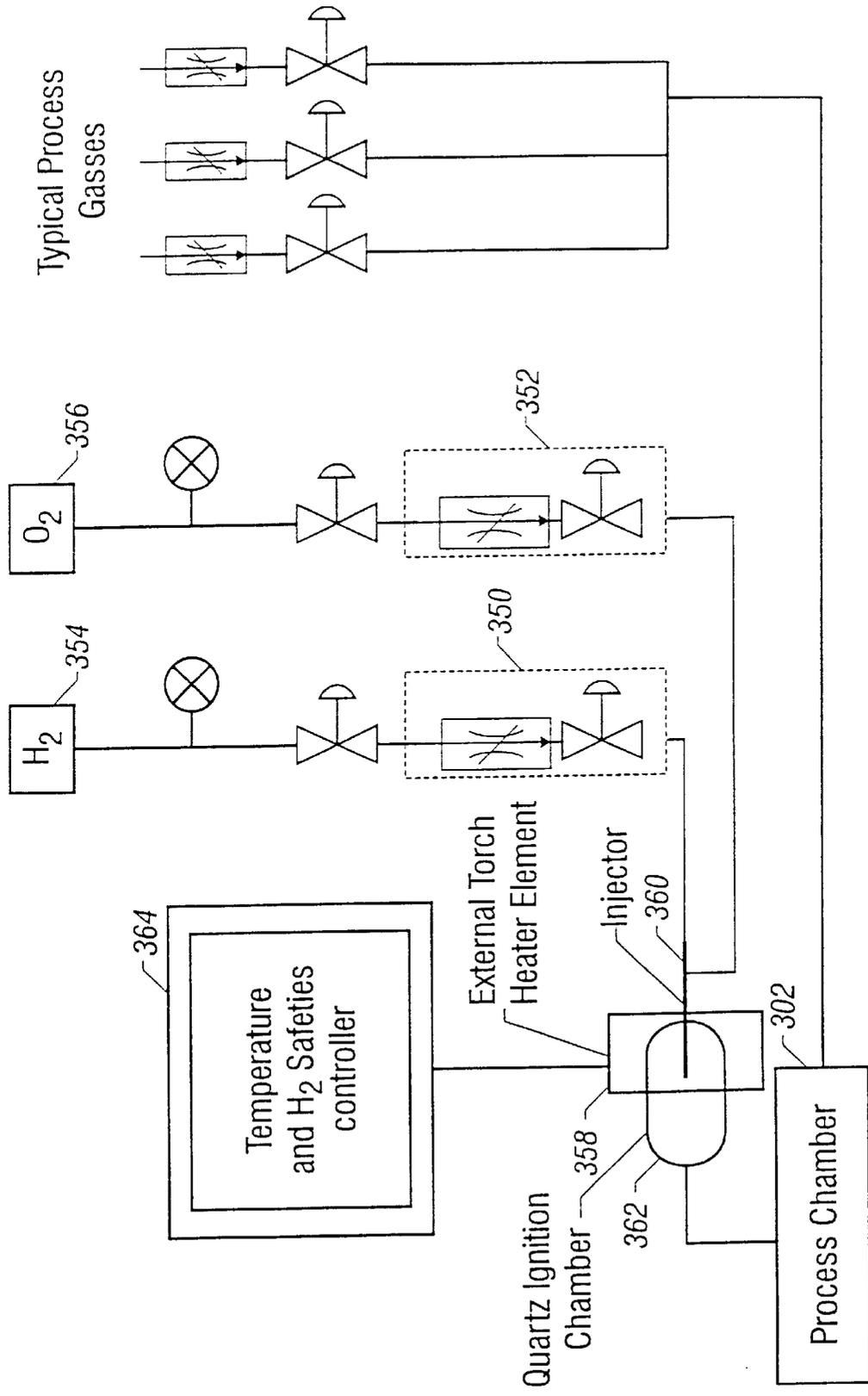


FIGURE 5

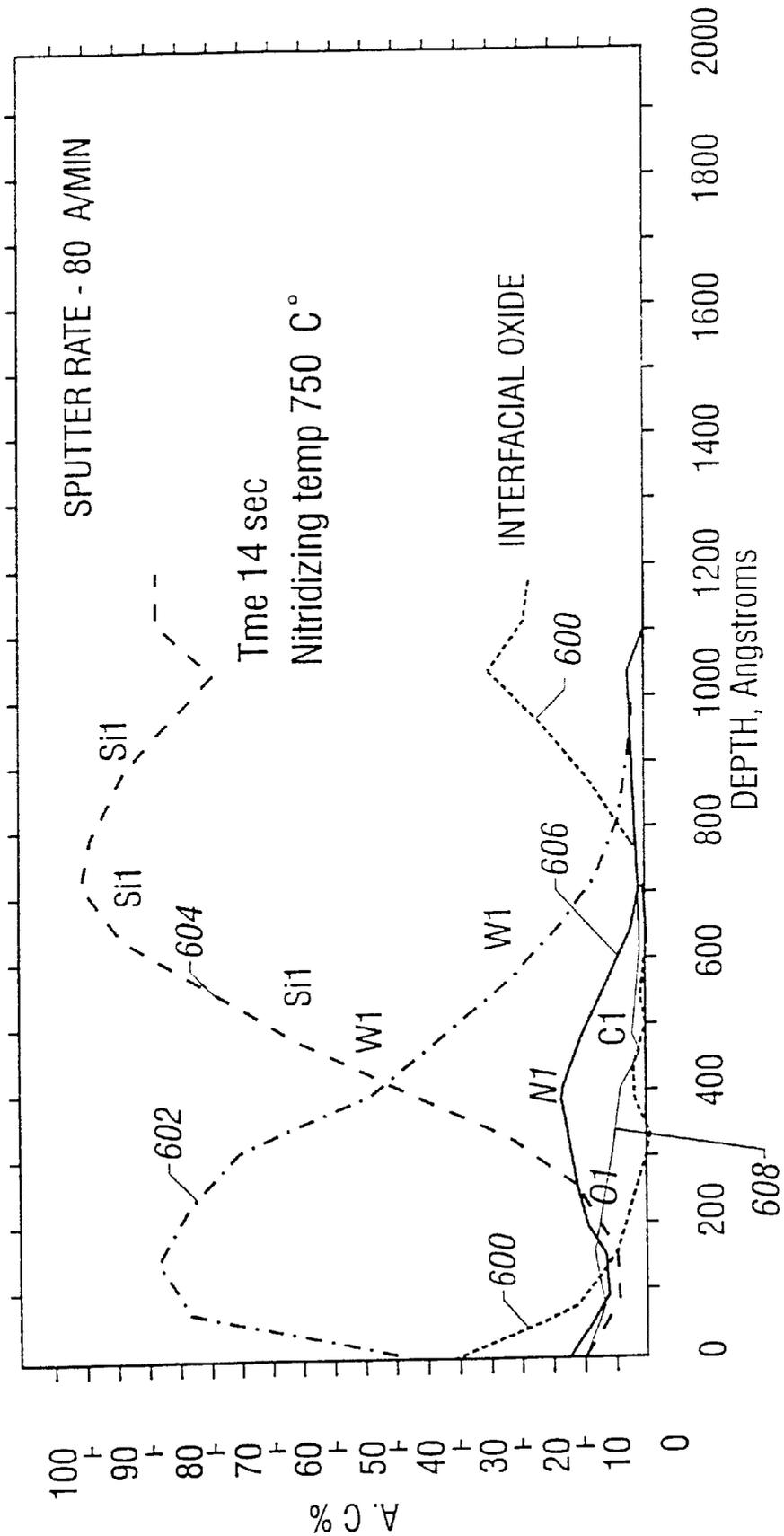


FIGURE 6

FORMING A CONDUCTIVE STRUCTURE IN A SEMICONDUCTOR DEVICE

This is a divisional of U.S. Ser. No. 09/031,407, filed Feb. 26, 1998, now U.S. Pat. No. 6,291,868.

BACKGROUND

The invention relates to forming a conductive structure in a semiconductor device.

Advanced integrated circuits in a semiconductor device require high speed interconnecting lines between circuits for improved device speed. Interconnecting lines are typically made of metal, e.g., aluminum, titanium. However, in some parts of a semiconductor device, particularly in regions where components are densely packed (such as the array of a memory device), or in regions where further heat steps are needed after formation of the interconnecting line during the manufacturing process, other materials are also widely used to form interconnecting lines, e.g., doped polysilicon or N+ or P+ diffused regions.

The different types of interconnecting lines exhibit different resistivities, with metal generally having the lowest resistivity. Polysilicon, which is also typically used as the conductive electrode at the gate of an N-channel or P-channel metal-oxide-silicon field effect transistor (MOSFET), exhibits a higher resistivity than metal.

As the speed requirements of semiconductors increase, the resistance of interconnecting lines, especially those formed of a higher resistivity material (such as polysilicon) reduces switching speeds of circuits in the device. The resistance of a line increases proportionately with its length. Thus, a polysilicon line running over a long length and connected to a large capacitive load, such as a wordline in a memory array connected to multiple transistors in the array, would cause a high RC delay during circuit switching.

One approach to reduce the resistivity of a polysilicon interconnect line is to use a polycide structure, in which a low resistance silicide (e.g., WSix) is formed on top of a doped polysilicon layer. This effectively forms a two-layer interconnect line in which the silicide layer provides a low resistivity conductive path.

Three-layer interconnecting lines have also been proposed, including a polymetal composite structure having tungsten (W) as the top layer, tungsten silicide nitride (WSiN) as the intermediate layer, and polysilicon as the bottom layer. The polymetal structure has a resistivity lower than the polycide structure that includes tungsten silicide on polysilicon.

SUMMARY

In general, according to one embodiment, a method of forming a conductive structure in a semiconductor device includes forming a lower electrically conductive layer on a support surface and forming an electrically conductive barrier over the lower layer. Further, an upper conductive layer is formed over the barrier layer, the upper conductive layer including metal silicide.

Other features and embodiments will become apparent from the following description and from the claims.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is an enlarged, cross-sectional view of a transistor in a semiconductor device.

FIG. 2 is a flow diagram of the fabrication steps for forming portions of the transistor structure of FIG. 1.

FIGS. 3, 4, and 5 are block diagrams of single-wafer rapid thermal processing systems for performing selective oxidation.

FIG. 6 is graph of an X-ray photoelectron spectrometer (XPS) surface analysis showing the selective oxidation region for a multilayer conductive structure.

DETAILED DESCRIPTION

Referring to FIG. 1, a multilayer, low resistivity conductive structure is described. The conductive structure can be used as part of the gate structure of a MOS transistor (as shown) or as an interconnecting line to connect circuits, such as a wordline used to connect transistors connected to memory cells in a memory array.

In FIG. 1, a transistor 12 is formed on a base 10, which includes a semiconductor (e.g., silicon) substrate or multilayer substrate (e.g., silicon-on-insulator or SOI substrate). The transistor 12 is adjacent a field oxide layer 110. The transistor includes source and drain regions 108A and 108B and a channel region 109. If the transistor 12 is used in a memory array, the source would be connected to a memory cell capacitor structure (not shown), while the drain would be connected to a digit line (not shown). The transistor 12 can also have many other uses in a semiconductor device.

A gate oxide layer 106 is formed above the channel region 109. A gate stack 112 is then formed over the gate oxide layer 106. In one embodiment, the gate structure 112 includes three electrically conductive layers (100, 102, 104) to reduce the resistivity of the gate. The three-layer structure can also be used to form an interconnecting line separate from the transistor 12, in which case the gate oxide layer 106 beneath the stack 112 would be replaced with other insulating layers.

The bottom conductive layer 104 is formed of a material that includes silicon, e.g., doped or undoped polysilicon, silicon germanium (SiGe), or amorphous silicon. The top conductive layer 100 includes a low resistivity material, which can be metal or metal silicide. Sandwiched between the top layer 100 and the bottom layer 104 is a conductive diffusion barrier layer 102 that is resistant to oxidation, agglomeration, and silicidation.

The barrier layer 102 acts to prevent agglomeration of silicon from the bottom layer 104 into the top conductive layer 100. For example, titanium silicide (TiSix) formed on polysilicon may result in agglomeration of silicon into the TiSix grains, which can increase resistivity. Silicidation can also occur between certain top layer and bottom layer materials, such as tungsten (W) formed on polysilicon, in which formation of higher resistivity WSix can occur.

The barrier layer 102 is formed of a material that includes metal silicide, metal nitride, or metal silicide nitride, such as tungsten silicide (WSix), tungsten silicide nitride (WSixNy), titanium silicide nitride (TiSixNy), tantalum silicide (TaSix), tantalum silicide nitride (TaSixNy), molybdenum silicide (MoSix), and molybdenum silicide nitride (MoSixNy), hafnium silicide (HfSix), hafnium silicide nitride (HfSixNy), zirconium silicide nitride (ZrSixNy), niobium silicide (NbSix), niobium silicide nitride (NbSixNy), and titanium nitride (TiNy).

Generally, a silicide, nitride, or silicide nitride composition is resistant to oxidation and is stable at high temperatures. The ability to withstand high temperatures is particularly important since the gate structure or interconnecting line is put through various subsequent high temperature process steps, including source-drain implant anneal, oxidation, and glass flow/reflow.

Metal silicides, nitrides, or silicide nitrides also have other desirable properties, including low resistivity, ease of formation, controlled oxidation properties, and stability in an oxidizing ambient. These materials also have excellent adhesion characteristics and exhibit low stress contacts.

The resistivity of a metal silicide, metal nitride, or metal silicide nitride barrier layer **102** is dependent on several factors, including the method of formation, annealing times and temperatures, and chemical purity. The stoichiometry of the refractory metal silicide, metal nitride, or metal silicide nitride composition can also affect resistivity; e.g., the x value of an $MSix$ composition and the x and y values of an $MSixNy$ composition can affect the resistivity.

In the barrier layer **102** containing an $MSixNy$ composition, the value of x for silicon can be set at a value greater than 2, while the value of y for nitrogen is set in the range between about 0.1 and 0.9, preferably between about 0.5–0.6. With higher y values, the $MSixNy$ compositions are more stable at higher temperatures, but the compositions also have higher resistivities.

The top conductive layer **100** can be made from low resistivity materials, e.g., metal or metal silicides, such as tungsten (W), cobalt (Co), titanium silicide ($TiSix$), cobalt silicide ($CoSix$), nickel silicide ($NiSix$), or other metal or metal silicide layers. Typically, the value of x may be greater than or equal to 2, with the exception of $NiSix$, where x can be equal to one. Generally, the metal silicide compositions are more stable at high temperatures than tungsten or cobalt, which tend to have relatively high oxidation rates.

The gate stack **112** and the gate oxide **106** are electrically insulated by side insulating spacers **114A** and **114B** and a top insulating layer **116**. The insulating materials can be formed using silicon nitride (Si_3N_4) or silicon dioxide (SiO_2).

Referring to FIG. 2, the fabrication flow of portions of the transistor **12** shown in FIG. 1 is illustrated. After the field oxide **110** and source-drain regions **108A** and **108B** are formed in the base **10**, the gate oxide **106** is formed on the surface of the base **10** (step **202**) by thermal growth or deposition such as chemical vapor deposition (CVD). The thickness of the gate oxide **106**, for current generation technologies, can typically range from about 30 angstroms (Å) to 150 Å.

Next, the bottom conductive layer **104** (which can include polysilicon, SiGex, or amorphous silicon) is formed, such as by deposition using a low pressure chemical vapor deposition (LPCVD) process. The bottom conductive layer **104** can have an exemplary thickness ranging from about 100 Å to 3,000 Å. The polysilicon, SiGex, or amorphous silicon layer **104** can also be doped with a dopant such as phosphorous or boron to improve electrical conductivity.

Next, the barrier layer **102** is formed (step **206**) to a thickness between about 50 Å to 500 Å, for example. Various methods can be used to form the diffusion barrier layer **102**, including using chemical vapor deposition (CVD), physical vapor deposition (PVD), or deposition followed by a high temperature anneal of a metal (e.g., tungsten or titanium) in an ambient containing nitrogen, ammonia (NH_3), or hydrazine (N_2H_4) in a rapid thermal processing (RTP) system.

Formation of metal silicide barrier layers using CVD may involve deposition of the metal onto the bottom conductive layer **104** followed by subsequent heating, which causes the metal and silicon containing material in the layer **104** to react to form a silicide. This type of silicide formation can yield low resistivity silicide layers.

To form a barrier layer **102** having metal silicide nitride ($MSixNy$) or metal nitride (MNy), the metal deposition onto

the bottom conductive layer step is followed by a high temperature (e.g., 600–1000° C.) anneal in an ambient including NH_3 or N_2H_4 . The NH_3 or N_2H_4 anneal can be performed in a rapid thermal processing (RTP) system for a predetermined amount of time, e.g., between about 1–60 seconds. If the metal deposited is tungsten on a polysilicon, SiGex, or amorphous silicon layer, the anneal step forms a barrier layer that contains Wsix and SiN, with no formation (or very little formation) of tungsten nitride (WN), as illustrated by the X-ray photoelectron spectrometer (XPS) profile graph shown in FIG. 6. Wsix and SiN are more oxidation resistant than WN or tungsten. The high temperature anneal can also be performed with a titanium on a silicon-containing material structure. The anneal in the NH_3 or N_2H_4 ambient forms a TiNy barrier layer.

FIG. 6 shows the percentage of materials present in a Wsix-polysilicon stack after anneal of a W/poly-Si structure in an NH_3 ambient at 750° C. The depth (as defined by an axis generally projecting perpendicularly from the surface of the base **10**) begins at the top surface (0 Å) of the stack **112** (without the top conductive layer **100**) and continues downwardly into the stack. A layer of tungsten is initially deposited on polysilicon. After anneal in the NH_3 , the layers formed include a tungsten layer **100** at the top and a Wsixny barrier layer **102** between the top tungsten layer and the bottom conductive layer **104**.

PVD by sputtering or evaporation can also be used to form metal silicides and metal silicide nitrides. The evaporation method utilizes simultaneous deposition of the metal and silicon (or metal, silicon and nitrogen) under high vacuum or sputtering of a metal silicide composite target. Sputtering of the metal and silicon (or metal, Si, and N) can be performed using RF or magnetron sputtering.

After formation of the barrier layer **102**, the metal or metal silicide conductive layer **100** is formed over the barrier layer **102** (step **208**), using either CVD or PVD techniques, for example. The conductive layer **100** can be formed to a thickness between about 200 Å to 2000 Å. Following formation of the top conductive layer **100**, the electrically insulating cap layer **116** is formed over the conductive layer **100** as an etch stop and oxidation barrier (step **210**). The insulating layer **116** can be formed using vapor deposited SiO_2 or Si_3N_4 . A dry etch process (such as reactive ion etching) is then used to form the gate stack (step **212**).

After the gate stack is formed, nitride insulating spacers **114A** and **114B** can optionally be formed using known methods, such as by LPCVD or PECVD nitride (step **214**). Oxide spacers can also be used, such as those formed using CVD with tetraethylorthosilicate (TEOS). Whether this step is performed depends on the type of materials used in forming the stack **112**.

For example, if a stack having a tungsten conductor on a titanium nitride barrier is used, then the spacers are useful as etch barriers as well as oxidation barriers in subsequent processing steps. The spacers **116A** and **116B** may also be used with other stacks that contain a metal conductor on a metal silicide or nitride barrier.

The spacer forming step **214** may not be needed when a stack having a metal silicide conductor on a metal silicide or metal silicide nitride barrier (e.g., $TiSix$ conductor on Wsix barrier) is used. With such stacks, the spacer formation is performed after the source-drain re-oxidation step (**216**).

The source-drain re-oxidation step (**216**) is performed to remove damage caused by reactive ion etching and patterning of the gate electrode. The re-oxidation step causes oxide

to be thermally grown on the sidewall of the etched polysilicon, SiGex, or amorphous silicon electrode, which also serves to thicken the gate oxide **106** at the gate edge to improve the gate oxide dielectric strength. The source-drain re-oxidation can be performed in the following environment: O_2 ; O_2/H_2 ; N_2O ; NO ; or a selective ambient, such as an H_2O/H_2 ambient in which the ratio of H_2O to H_2 is controlled to predetermined ranges.

If the top conductive layer **100** is formed of a metal silicide material, and the barrier layer **102** is formed of a metal silicide or metal silicide nitride material, then the two layers are relatively resistant to oxidation and any of the source-drain re-oxidation techniques listed above can be used. However, certain materials that can be used in the top conduction layer **100**, such as tungsten (W) or titanium (Ti), and certain materials in the barrier layer **102**, such as a metal nitride (e.g., TiN), have relatively high oxidation rates.

For example, tungsten oxidation rate is much faster than that of silicon, and typical oxidation processes can cause the volume of tungsten oxide (WO_3) to be much larger than that of W. If WO_3 formation occurs, peeling or morphological degradation of the tungsten film may occur. Thus, in cases where the top conduction layer **100** has a relatively high oxidation rate, a selective oxidation process is preferred over conventional oxidation or wet oxidation. Similar issues exist when titanium is used as the top conduction layer **100**.

Possible metal nitride materials (in addition to the materials discussed above) for the barrier layer **102** include tungsten nitride (WN) or titanium nitride (TiN), which are susceptible to relatively fast oxidation. If such barrier layers are used, then selective oxidation may be particularly advantageous. However, even if metal silicide top conductive layers **100** or metal silicide or metal silicide nitride barrier layers **102** are used, the selective oxidation process may also help to reduce the rate of oxidation of those materials.

Selective source drain re-oxidation can be performed in a water vapor ambient with controlled amounts of hydrogen added in a single-wafer rapid thermal processing (RTP) system (e.g., an AG8108 Heat Pulse RTP system) for selective oxidation of silicon over the metal, metal silicide, metal silicide nitride, or metal nitride top conducting layer **100** or barrier layer **102**. In addition, use of a single-wafer system, such as the three types shown in FIGS. 3–5, provide several advantages over use of a furnace that can receive multiple wafers. In a single-wafer RTP system, better control of process conditions can be achieved. For example, better uniformity of temperature can be achieved over the entire surface of the wafer, which is particularly advantageous when large wafers (e.g., 300 mm wafers) are used. In addition, better ambient control and uniformity of oxidation over the entire processed surface of a wafer can be achieved.

The described selective oxidation processes (shown in FIGS. 3, 4, and 5) can also be applied to multi-wafer furnace systems.

Referring to FIG. 3, an RTP single-wafer system uses an ambient of argon-hydrogen ($Ar-H_2$) and water vapor. Other inert gases besides Ar can also be used. By controlling the ratio of H_2O to O_2 , use of this ambient can reduce oxidation of a metal (e.g., tungsten) top conductive layer **100** and WN, Wsixny, TiN, and other metal nitride conductive diffusion barrier layers **102**.

A quartz vessel **300** (which can contain 20 liters of liquid) is filled approximately half full of deionized water through a liquid flow controller **304** from a source **306**. The vessel **300** is then heated and maintained at an elevated temperature, e.g., between about 95–98° C., through use of

an external heating blanket **314** affixed to the outside of the quartz vessel **300**. The elevated temperature evaporates portions of the deionized water.

The temperature of the deionized water in the vessel **300** is monitored by a thermocouple **308** inserted into a sheath in the quartz vessel **300**. The over temperature trip level of the thermocouple **308** can be set at about 120° C. The thermocouple **308** is connected to a temperature and water level controller **310** for monitoring. The controller **310** adjusts the temperature of the blanket **314** as the liquid temperature in the vessel **300** varies. Over temperature thermocouples (not shown) can also monitor the heater blanket **314** temperature to prevent heater blanket temperature runaway.

The level of the deionized water in the vessel **300** is monitored by a liquid level sensor **312**, also connected to the controller **310**. The controller **310** adjusts the flow rate through the flow controller **304** to maintain the level of the liquid in the vessel **300**. The autofill feature for the deionized water is disabled during a process run (to perform the source drain re-oxidation) so as not to disturb the water vapor delivery.

Delivery of the deionized water vapor is achieved by injecting an $Ar-H_2$ mixture into the vessel **300** through a mass flow controller **322** at a predetermined rate. The $Ar-H_2$ comes from a source **318**. The H_2 can originate from a pure hydrogen source or from a breakdown of a hydrogen containing compound such as NH_3 or N_2H_4 . The resulting water and argon vapor is transported through a line **316** (which can be a ½ inch heat taped stainless steel line) maintained at a predetermined temperature, e.g., about 110° C., to prevent recondensation of the vapor.

The vapor in the line **316** flows through a vapor flow controller **324** to a single-wafer process chamber **302**. Other conventional RTP process gases are also provided through flow controllers **326** to the processor chamber **302**. The flow of H_2O can be selected to be in the range between about 1 SCCM (standard cubic centimeters per minute) and 50 SLM (standard liters per minute), with a preferred range of about 1 SCCM to 10 SLM. The flow rate of H_2 can be selected to a value in the range between about 1 SCCM and 50 SLM, with a preferred range of about 1 SCCM to 20 SLM. In the AG8108 system, the H_2O/H_2 partial pressure ratio can be maintained between about 2.3 and 2.8. However, the ratios vary according to the specific types of RTP systems used. The processing temperature in the single-wafer processing chamber can be maintained between about 950° C. and 1100° C. Selective oxidation of silicon over tungsten of about 2:1 can be achieved using the system of FIG. 3.

Referring to FIG. 4, an alternative single-wafer RTP system performs source-drain selective re-oxidation using a different transport system. Elements that are the same as in the RTP system of FIG. 1 have common reference numerals. As in the RTP system of FIG. 1, a predetermined amount of deionized water is kept in the vessel **300** (e.g., half full in a 20-liter vessel). However, delivery of the deionized water vapor is achieved through the use of a vapor flow controller **330**, rather than through use of the mass flow controller **322** to pump argon **318** into the vessel **300** to move vapor through the line **316**. The pressure in the water vessel **300** can be approximately 960 Torr, which is sufficient to generate ample flow through the vapor flow controller **330**. The vapor is then transported through the line **316** to the process chamber **302**, with the line temperature maintained at about 110° C. to prevent recondensation of the vapor. Hydrogen is passed through one of the vapor flow controllers **326** to the process chamber **302** to perform selective oxidation of silicon over other materials.

Referring to FIG. 5, an RTP system with an external torch assembly is used to create the water vapor flow for selective oxidation. Hydrogen (H₂) and oxygen (O₂) are delivered through vapor flow controllers 350 and 352, respectively, from sources 354 and 356, respectively. The H₂ and O₂ are delivered to an injector 360 inserted into the external torch assembly 358. The torch assembly 358 is maintained at a temperature of about 900° C. to provide ignition energy. The resulting water vapor and H₂ mixture is delivered to the single-wafer process chamber 302 via a quartz tube interface 362.

As is the case with the RTP system of FIG. 3, the RTP systems of FIGS. 4 and 5 also maintain a predetermined H₂O/H₂ partial pressure ratio and temperature.

In the RTP system of FIG. 5, safety measures are provided by an external controller 364, which monitors and maintains the external torch element temperature and provides over temperature and runaway safeties. The controller 364 can also implement steps to ensure safety associated with using H₂ as a process gas. The safety mechanisms implemented include maintaining a particular H₂/O₂ ratio. Thus, H₂ flow is disabled if no O₂ is present; H₂ is disabled if the torch temperature is below 700° C.; an initial nitrogen (N₂) purge is performed of the injector 360 before the flow of H₂ is turned on; and H₂ leak detectors are used to determine when to turn off and purge the H₂ line if an H₂ leak is detected. The controller 364 also monitors the temperature of the process chamber 302 to prevent water vapor from being formed if the process chamber 302 is below 700° C. to prevent recondensation of the water vapor.

Other embodiments are also within the scope of the following claims. Although the layers in the multilayer conductive structure have been described with certain thicknesses for each layer, it is contemplated that the layer thicknesses can be varied and still achieve desirable results. The conductive structure described can be formed with a stack having more than three layers. Further, various systems and processes have been described with particular parameters; these parameters can also be varied. The systems described have components associated with certain, specific parameters and values, which can be varied.

What is claimed is:

1. A method of forming a multi-layer conductive structure in a semiconductor device, the method comprising: forming a first layer containing silicon; depositing a metal layer over the first layer; and annealing the metal layer in an ambient having a composition selected from a group consisting of nitrogen, NH₃, and hydrazine, wherein a second layer containing metal silicide nitride is formed over the first layer after annealing.
2. A method of forming a multi-layer conductive structure in a semiconductor device, the method comprising: forming a first layer containing silicon; depositing a metal layer over the first layer; annealing the metal layer in an ambient having a composition selected from a group consisting of nitrogen, NH₃, and hydrazine, wherein a second layer containing silicide is formed over the first layer after annealing; and forming a top conductive layer over the second layer.
3. The method of claim 2, wherein the first layer, second layer, and top conductive layer form the multi-layer conductive structure.
4. A method of forming a conductive structure in a semiconductor device, the method comprising:

forming a lower electrically conductive layer on a support surface;

forming an electrically conductive barrier layer over the lower layer, the barrier layer containing metal silicide nitride, MSixNy, wherein x is greater than about 2 and y ranges between about 0.1 and 0.9; and

forming an upper conductive layer over the barrier layer, the upper conductive layer including metal silicide.

5. The method of claim 4, wherein the lower layer includes silicon.

6. The method of claim 4, wherein the lower layer includes a material selected from the group consisting of polysilicon, SiGex, and amorphous silicon.

7. The method of claim 4, wherein the upper conductive layer includes a material selected from the group consisting of TiSix, CoSix, NiSix, and PdSix.

8. A method of forming a conductive structure in a semiconductor device, comprising:

forming a first electrically conductive layer on a base;

forming a barrier layer over the first layer, the barrier layer including a metal silicide composition without nitrogen and having a thickness between about 50 Å and 500 Å; and

forming a second electrically conductive layer over the barrier layer.

9. The method of claim 8, wherein forming the barrier layer includes using chemical vapor deposition.

10. The method of claim 8, wherein forming the barrier layer includes using physical vapor deposition.

11. A method of forming a conductive structure in a semiconductor device, comprising:

forming a first electrically conductive layer on a base;

forming a barrier layer over the first layer, the barrier layer including a metal silicide composition and having a thickness between about 50 Å and 500 Å; and

forming a second electrically conductive layer over the barrier layer,

wherein forming the barrier layer includes depositing a metal on a layer containing silicon and controlling the metal-silicon structure in a preselected ambient.

12. The method of claim 11, wherein the preselected ambient includes NH₃.

13. The method of claim 11, wherein the preselected ambient includes hydrazine.

14. The method of claim 11, wherein the preselected ambient includes nitrogen.

15. The method of claim 4, wherein forming the barrier layer comprises forming a barrier layer containing a material selected from the group consisting of tungsten silicide nitride, titanium silicide nitride, tantalum silicide nitride, molybdenum silicide nitride, hafnium silicide nitride, zirconium silicide nitride, and niobium silicide nitride.

16. A method of forming a conductive structure in a semiconductor device, comprising:

forming a first electrically conductive layer on a base;

forming a barrier layer over the first layer, the barrier layer including a metal silicide composition and having a thickness between about 50 Å and 500 Å; and

forming a second electrically conductive layer over the barrier layer,

wherein forming the barrier layer comprises forming a barrier layer containing a material selected from the group consisting of tungsten silicide, tantalum silicide, molybdenum silicide, hafnium silicide, and niobium silicide.

17. A method of making a semiconductor device, the method comprising:
 forming a gate structure of a transistor, wherein forming the gate structure comprises:
 forming a lower electrically conductive layer on a support surface,
 forming an electrically conductive barrier layer over the lower layer, the barrier layer containing metal silicide nitride, $MSixNy$, where x is greater than about 2 and y ranges between about 0.1 and 0.9, and forming an upper conductive layer over the barrier layer.
18. The method of claim 17, wherein forming the upper layer comprises forming a layer containing metal silicide.
19. A method of forming a multi-layer conductive structure in a semiconductor device, comprising:
 forming a first layer containing silicon;
 forming a barrier layer containing metal silicide nitride over the first layer by depositing a metal layer over the first layer and annealing the metal layer in an ambient having a composition selected from the group consisting of nitrogen, NH_3 , and hydrazine; and
 forming an upper conductive layer over the barrier layer.
20. The method of claim 19, further comprising forming a gate structure of a transistor that comprises the acts of forming the first layer, forming the barrier layer, and forming an upper conductive layer.
21. A method of forming a conductive structure in a semiconductor device, comprising:
 forming a first layer containing silicon;

- forming a barrier layer over the first layer by depositing a metal layer over the first layer and annealing the metal layer in an ambient having a composition selected from the group consisting of nitrogen, NH_3 , and hydrazine; and
 forming an upper conductive layer over the barrier layer.
22. A method of forming a semiconductor device, comprising:
 forming a gate structure of a transistor, the gate structure having lower and upper electrically conductive layers and a barrier layer between the lower and upper electrically conductive layers;
 forming the barrier layer to consist essentially of a metal silicide selected from the group consisting of tantalum silicide, molybdenum silicide, hafnium silicide, and niobium silicide; and
 forming the upper electrically conductive layer to have a nickel silicide, $NiSin$, where n is at least about one.
23. The method of claim 4, wherein forming the upper conductive layer including metal silicide comprises forming the upper conductive layer including metal silicide, $MSin$, where n is at least about one.
24. The method of claim 4, wherein forming the upper conductive layer including metal silicide comprises forming the upper conductive layer including metal silicide, $MSin$, where n is greater than or equal to about 2.
25. The method of claim 4, wherein forming the barrier layer comprises forming a barrier layer having metal silicide nitride, $MSixNy$, where y ranges between about 0.5 and 0.6.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,362,086 B2
DATED : March 26, 2002
INVENTOR(S) : Ronald A. Weimer et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 8,

Line 58, "suicide" should be -- silicide --.

Signed and Sealed this

Fifteenth Day of July, 2003

A handwritten signature in black ink, appearing to read "James E. Rogan", written over a horizontal line.

JAMES E. ROGAN
Director of the United States Patent and Trademark Office